

Features

- Frequency: 0.4~3.5GHz
- Gain: 17.5dB
- Output P_{1dB}: 15dBm
- Supply Voltage: +5V@54mA
- Die Size: 1.2mm×1.25mm×0.1mm

Typical Applications

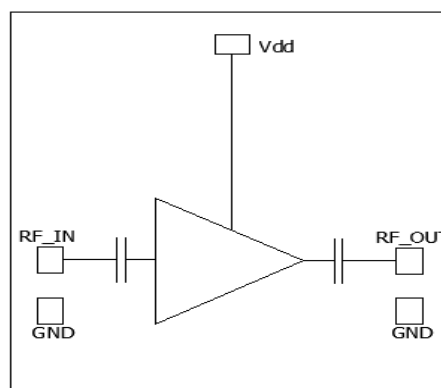
- Microwave radio including point to point communication
- Telecommunication
- Weather radar
- Optical communication
- Test instrumentation
- SatCom
- VSAT
- Military and Aerospace

General Description

The XT3008A is a GaAs MMIC Low Noise Amplifier die which operates between 0.4GHz~3.5GHz. The amplifier can provide 17.5dB gain, 15dBm Output P_{1dB}, 1.2dB noise figure from a 54 mA supply current.

The chip offers full passivation for increased reliability and moisture protection. This amplifier is the perfect alternative to higher cost hybrid amplifiers.

Functional Diagram



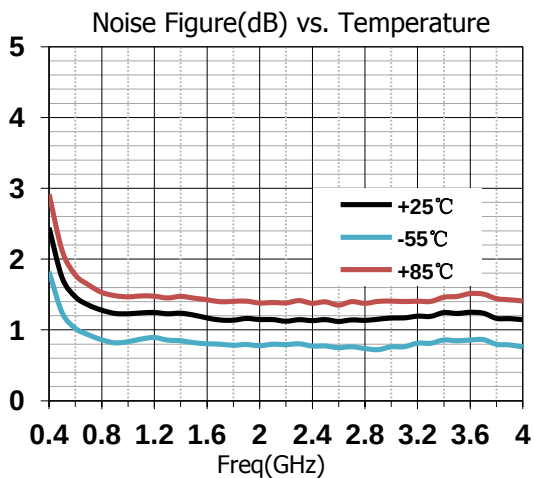
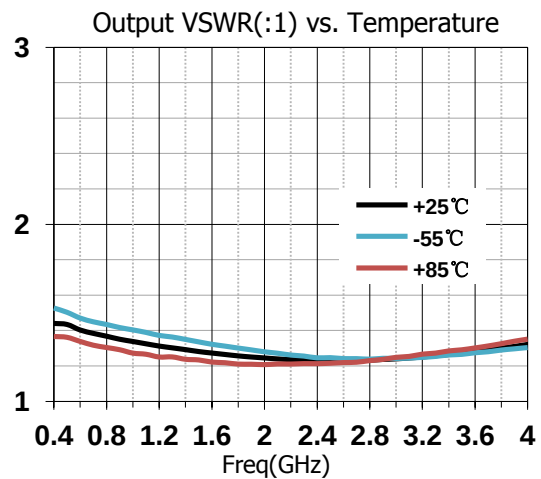
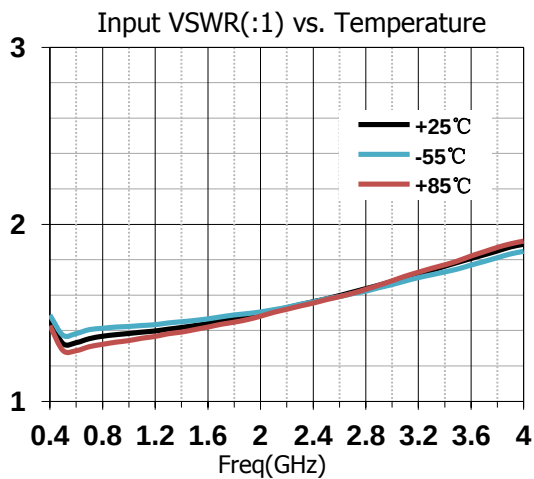
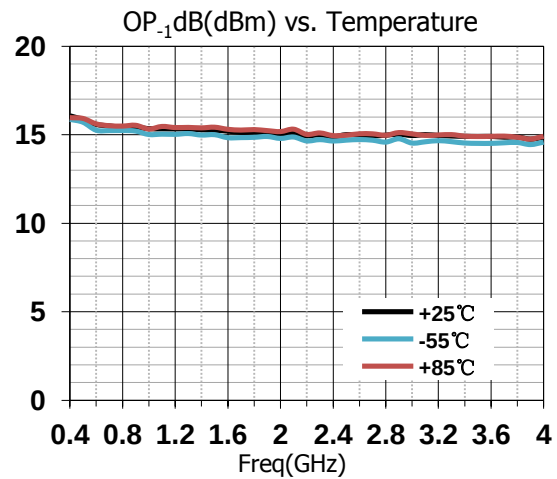
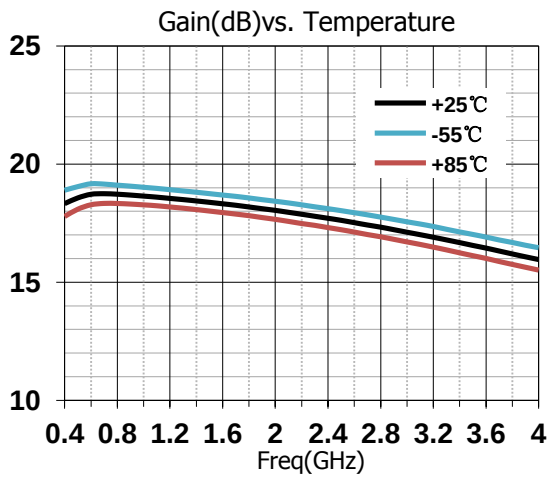
Electrical Performance (T_A=25°C, V_D= +5V, I_D=54mA, Z₀=50Ω)

Parameter	Min.	Typ.	Max.	Units
Frequency Range	0.4~3.5			GHz
Gain	15	17.5	20	dB
Gain Flatness	—	±1	±2	dB
Reverse Isolation	—	20	—	dB
Input/Output VSWR	—	1.4	1.8	:1
Noise Figure	—	1.2	3	dB
Output Power for 1 dB Compression (OP _{1dB})	13	15	—	dBm
Output Third Order Intercept (OIP ₃)	—	25	—	dBm
Supply Current(I _D)	—	54	—	mA

Absolute Maximum Ratings

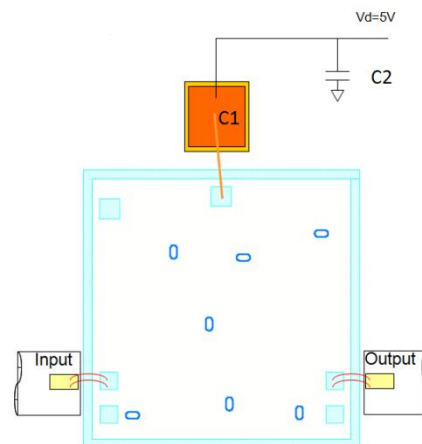
Maximum Input Power	+15dBm	Operating Temperature	-55°C~+85°C
Channel Temperature	+150°C	Storage Temperature	-65°C~+150°C

Typical Performance Curve



Rev 2.0

Assembly Diagram



Reference Des.	Value	Part Number	Manuf.	Size
C1	300pF	CHIP CAPACITOR	RADVISTA	—
C2	10nF	GRM155R71H103KA88D	MURATA	0402

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.